

# **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
I <sub>C</sub>	Collector Current - Continuous	1.2	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Ν	lax	Units
		2N6427	*MMBT6427	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/∘CCC
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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(continued)

TERISTICS			·	
ector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
ector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	40		V
tter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	12		V
ector Cutoff Current	$V_{CE} = 25 \text{ V}, \text{ I}_{B} = 0$		1.0	μA
ector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		50	nA
tter Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$		50	nA
	ector-Base Breakdown Voltage tter-Base Breakdown Voltage ector Cutoff Current ector Cutoff Current tter Cutoff Current	tter-Base Breakdown Voltage $I_E = 10 \ \mu A, I_C = 0$ ector Cutoff Current $V_{CE} = 25 \ V, I_B = 0$ ector Cutoff Current $V_{CB} = 30 \ V, I_E = 0$	tter-Base Breakdown Voltage $I_E = 10 \ \mu$ A, $I_C = 0$ 12ector Cutoff Current $V_{CE} = 25 \ V$ , $I_B = 0$ ector Cutoff Current $V_{CB} = 30 \ V$ , $I_E = 0$	tter-Base Breakdown Voltage $I_E = 10 \ \mu$ A, $I_C = 0$ 12ector Cutoff Current $V_{CE} = 25 \ V$ , $I_B = 0$ 1.0ector Cutoff Current $V_{CB} = 30 \ V$ , $I_E = 0$ 50

	$v_{EB} = 10 v, I_C = 0$		50	nA
ACTERISTICS				
DC Current Gain*	I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V	10,000	100,000	
	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$	20,000	200,000	
	$I_{C} = 500 \text{ mA}, V_{CE} = 5.0 \text{ V}$	14,000	140,000	
Collector-Emitter Saturation Voltage	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.2	V
-	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.5	V
Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
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## SMALL SIGNAL CHARACTERISTICS

Base-Emitter On Voltage

V<sub>CE(sat)</sub>

V<sub>BE(sat)</sub>

V<sub>BE(on)</sub>

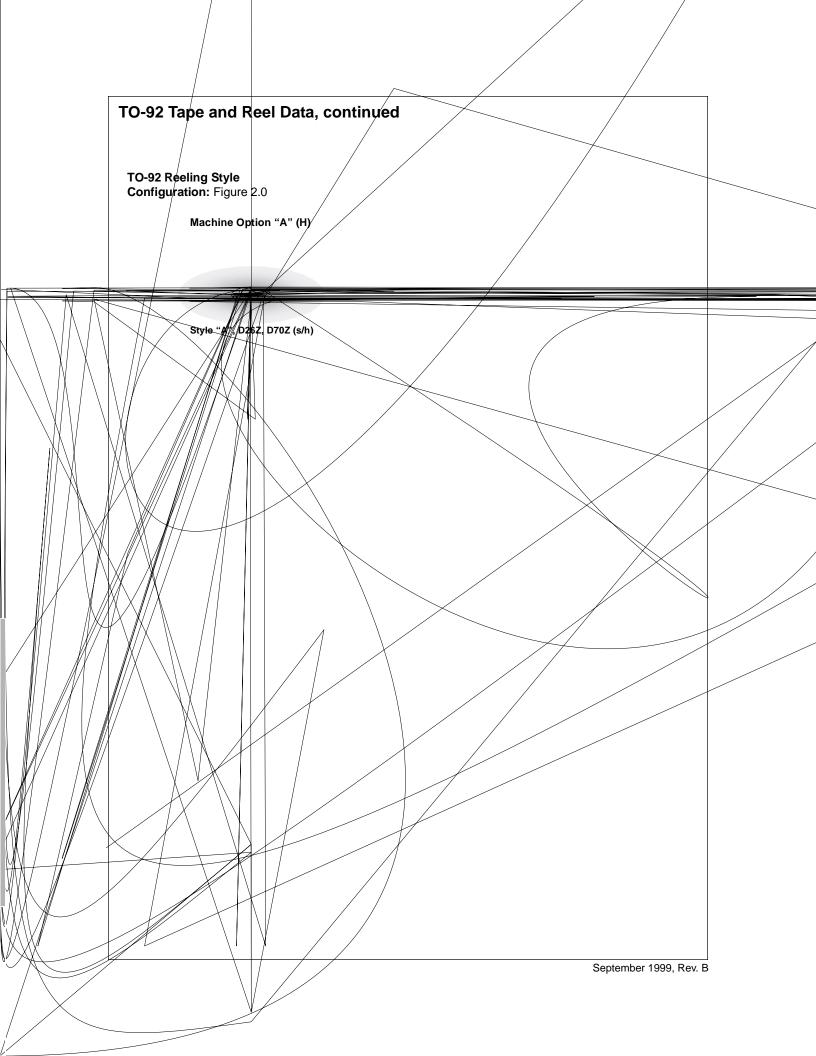
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ f = 1.0 MHz	7.0	pF
C <sub>ibo</sub>	Input Capcitance	$V_{BE} = 1.0 \text{ V}, I_{C} = 0,$ f = 1.0 MHz	15	pF

 $I_{C}$  = 50 mA,  $V_{CE}$  = 5.0 mA

\*Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%

2N6427 / MMBT6427







July 1999, Rev. A



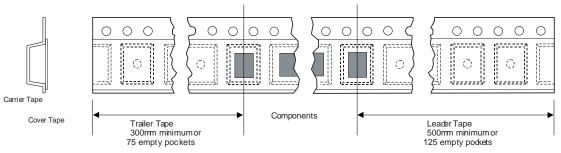
SOT-23 Packaging Configuration: Figure 10

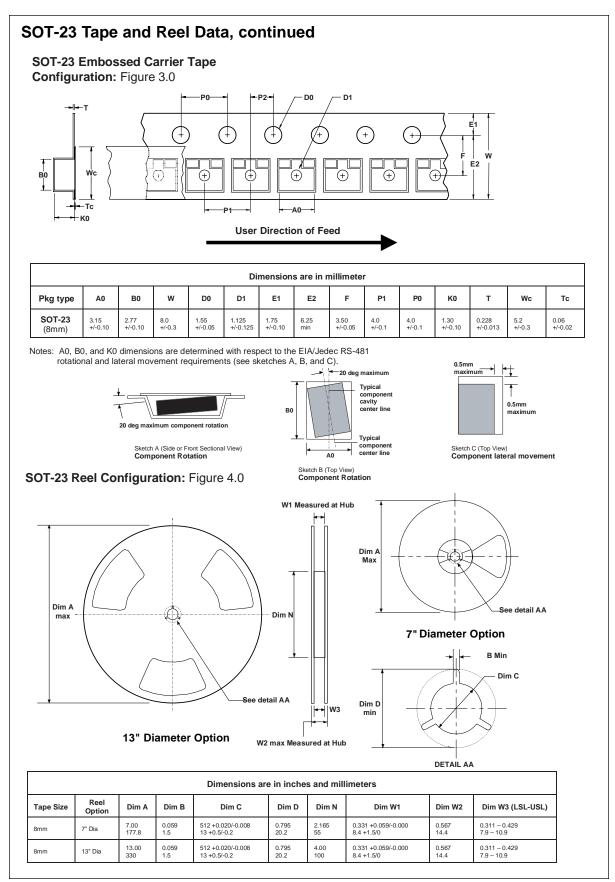
SOT-23 PackagingInformation				
PackagingOption	Standard (noflow code)	D87Z		
Packagingtype	TNR	TNR		
Qty per Reel/Tube/Bag	3,000	10,000		
Reel Size	7" Dia	13"		
Box Dimension (mm)	187x107x183	343x343x64		
Max qty per Box	24,000	30,000		
Weight per unit (gm)	0.0082	0.0082		
Weight per Reel (kg)	0.1175	0.4006		
Note/Comments				



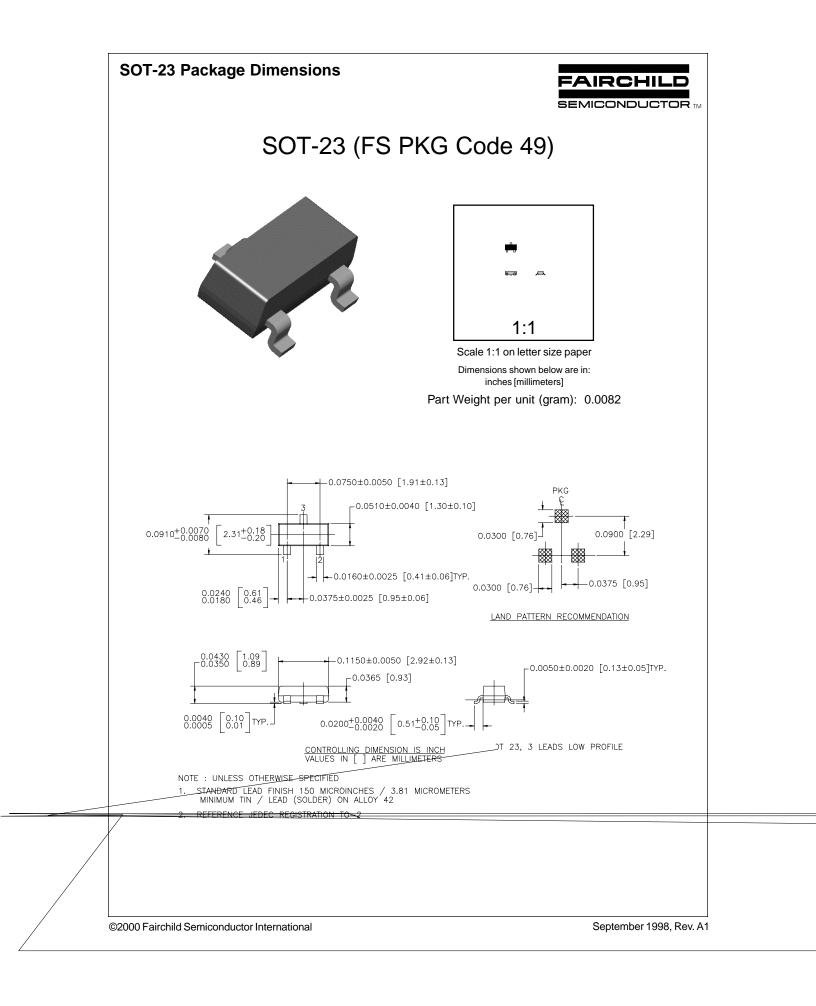


## SOT-23 Tape Leader and Trailer Configuration: Figure 20





September 1999, Rev. C



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